

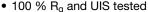
N-Channel 30 V (D-S) MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.00210					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00286					
Q _g typ. (nC)	19.7					
I _D (A) a, g	60 ^{a, g}					
Configuration	Single					

FEATURES

- TrenchFET® Gen IV power MOSFET
- Optimized Q_g, Q_{gd}, and Q_{gd}/Q_{gs} ratio reduces switching related power loss

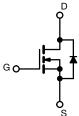






APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- VRMs and embedded DC/DC
- · Synchronous buck converter
- · Load switching



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8
Lead (Pb)-free and halogen-free	SiRA64DP-T1-RE3

ABSOLUTE MAXIMUM RATINGS (T	A = 25 °C, unless	s otherwise not	ed)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	30	V
Gate-source voltage		V_{GS}	+20, -16	V
	T _C = 25 °C		60 g	
Continuous drain current (T _J = 150 °C)	T _C = 70 °C] , [60 g	
	T _A = 25 °C	I _D	37 b, c	
	T _A = 70 °C	1	30 b, c	
Pulsed drain current (t = 100 μs)		I _{DM}	100	A
Continuous source-drain diode current	T _C = 25 °C		23 ^g	
Continuous source-drain diode current	T _A = 25 °C	l _S	4.2 b, c	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	30	
Single pulse avalanche energy	L = 0.1 min	E _{AS}	45	mJ
	T _C = 25 °C		27.8	
Maximum navver discination	T _C = 70 °C] _ [17.8	10/
Maximum power dissipation	T _A = 25 °C	P _D	5 b, c	W
	T _A = 70 °C	1	3.2 b, c	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) d, e			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R_{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	3.4	4.5	C/ VV

- a. Based on T_C = 25 °C
- b. Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile (www.vishav.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 70 °C/W
- Package limited



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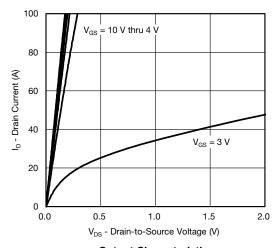
SPECIFICATIONS (T _J = 25 °C, t		,			1	
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	T		<u> </u>	T	1	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA	-	18	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_{J}$.D =00 p. 1	-	-6.2	-	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.1	-	2.2	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +20 \text{ V}, -16 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	lnoo L	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
	I _{DSS}	V= 30 V, $V_{DS GS} = 0 V$, $T_J = 55 ^{\circ}C$	-	-	10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40	-	-	Α
Decision and the second of the	Ь	V _{GS} = 10 V, I _D = 10 A	-	0.00180	0.00210	0
Drain-source on-state resistance a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	0.00220	0.00286	Ω
Forward transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 10 A	-	70	-	S
Dynamic ^b				•		
Input capacitance	C _{iss}		-	3420	-	
Output capacitance	C _{oss}		-	1100	-	pF
Reverse transfer capacitance	C _{rss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	81	-	
C _{rss} /C _{iss} ratio			_	0.024	0.048	
		V = 15 V, V _{GS} = 10 V, I _D = 10 A	-	43	65	
Total gate charge	Q _g		-	19.7	30	
Gate-source charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	8.1	-	nC
Gate-drain charge	Q _{gd}		-	2.9	-	
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	-	37	-	
Gate resistance	Rg	f = 1 MHz	0.2	0.8	1.6	Ω
Turn-on delay time	t _{d(on)}		-	13	25	
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_{I} = 1.5 \Omega$	_	15	30	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	25	50	
Fall time	t _f		-	10	20	
Turn-on delay time	t _{d(on)}		-	24	48	ns
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_L = 1.5 \Omega$	-	45	70	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	30	60	
Fall time	t _f			15	30	
Drain-Source Body Diode Characteristic				1		
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	23	
Pulse diode forward current (t = 100 μs)	I _{SM}	-	-	-	100	Α
Body diode voltage	V _{SD}	I _S = 10 A	-	0.73	1.2	V
Body diode reverse recovery time	t _{rr}	<u> </u>	_	40	80	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	_	34	70	nC
Reverse recovery fall time	t _a	$T_{\rm J} = 25 ^{\circ}{\rm C}$	_	20	-	
Reverse recovery rise time	+	Ç	_	20	_	ns
neverse recovery rise time	t _b		_	20	_	

Notes

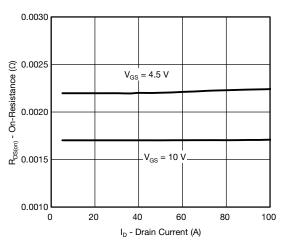
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

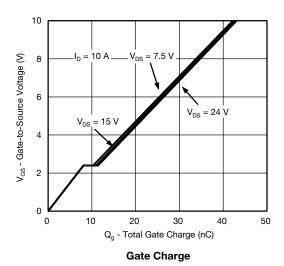


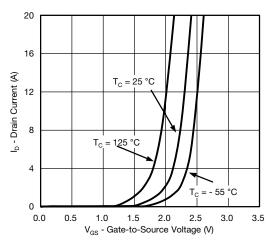


Output Characteristics

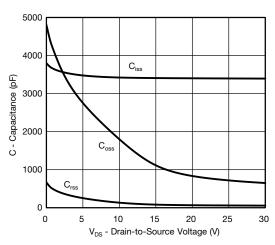


On-Resistance vs. Drain Current

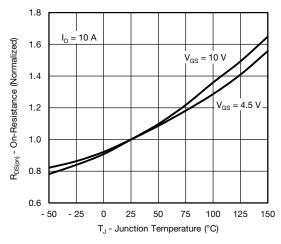




Transfer Characteristics

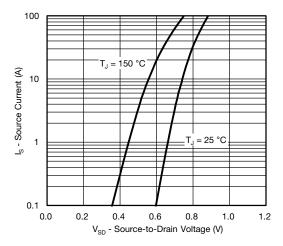


Capacitance

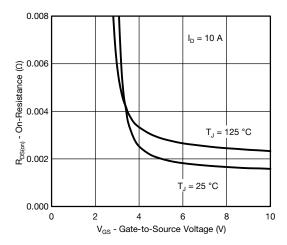


On-Resistance vs. Junction Temperature

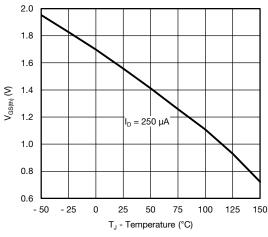




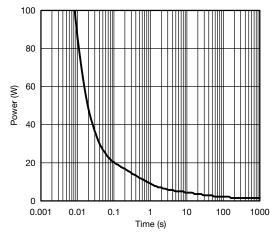
Source-Drain Diode Forward Voltage



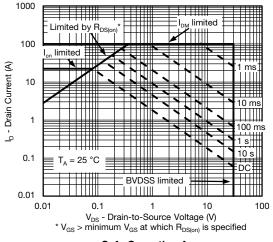
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

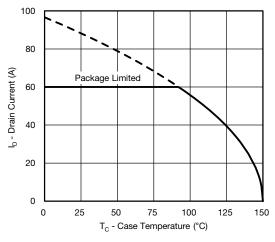


Single Pulse Power, Junction-to-Ambient



Safe Operating Area

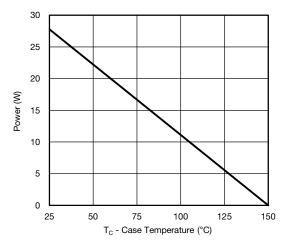




Current Derating a

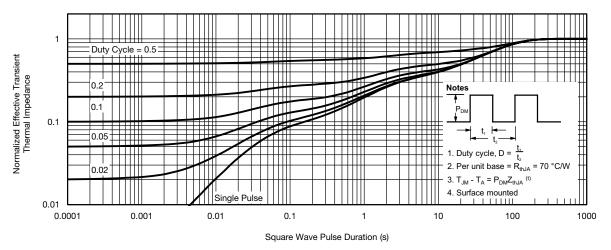
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

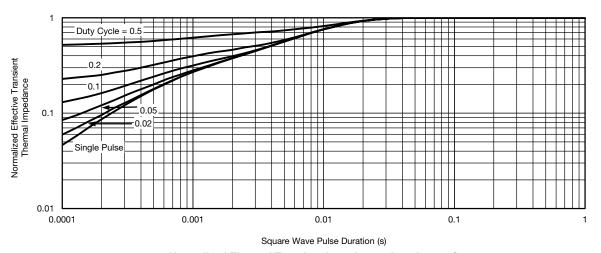


Power, Junction-to-Case





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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DWG: 5881

PowerPAK® SO-8, (Single/Dual)

Notes 1. Inch will govern. 2 Dimensions exclusive of mold gate burrs.

3. Dimensions exclusive of mold flash and cutting burrs.

Backside View of Dual Pad

DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX	
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	_	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4		0.57 typ.		0.0225 typ.			
D5		3.98 typ. 0.15					
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4		0.75 typ.			0.030 typ.		
е		1.27 BSC			0.050 BSC		
K		1.27 typ.			0.050 typ.		
K1	0.56	-	-	0.022	-	-	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М		0.125 typ.			0.005 typ.		

Revison: 13-Feb-17 1 Document Number: 71655



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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